

SN74LVC16241**16-BIT BUFFER/DRIVER****WITH 3-STATE OUTPUTS**

SCAS348A - MARCH 1994 - REVISED JULY 1995

- Member of the Texas Instruments Widebus™ Family
- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC16241 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. This device provides true outputs and complementary output-enable (OE and \overline{OE}) inputs.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVC16241 is characterized for operation from -40°C to 85°C.

**DGG OR DL PACKAGE
(TOP VIEW)**

1	1	48	2OE
1Y1	2	47	1A1
1Y2	3	46	1A2
GND	4	45	GND
1Y3	5	44	1A3
1Y4	6	43	1A4
V _{CC}	7	42	V _{CC}
2Y1	8	41	2A1
2Y2	9	40	2A2
GND	10	39	GND
2Y3	11	38	2A3
2Y4	12	37	2A4
3Y1	13	36	3A1
3Y2	14	35	3A2
GND	15	34	GND
3Y3	16	33	3A3
3Y4	17	32	3A4
V _{CC}	18	31	V _{CC}
4Y1	19	30	4A1
4Y2	20	29	4A2
GND	21	28	GND
4Y3	22	27	4A3
4Y4	23	26	4A4
4OE	24	25	3OE

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

PRODUCT PREVIEW information concerns products in the formative or design phase of development. Characteristic data and other specifications are design goals. Texas Instruments reserves the right to change or discontinue these products without notice.

Copyright © 1995, Texas Instruments Incorporated



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

SN74LVC16241
16-BIT BUFFER/DRIVER
WITH 3-STATE OUTPUTS

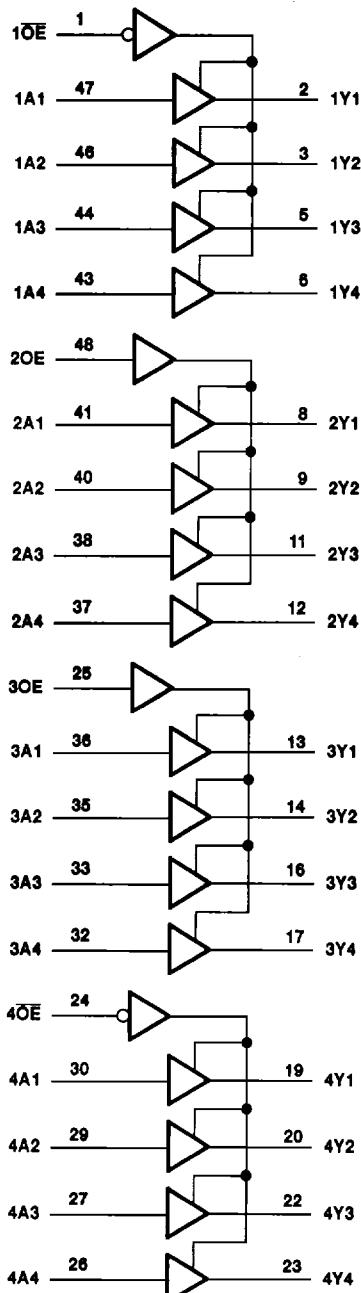
SCAS348A - MARCH 1994 - REVISED JULY 1995

FUNCTION TABLES

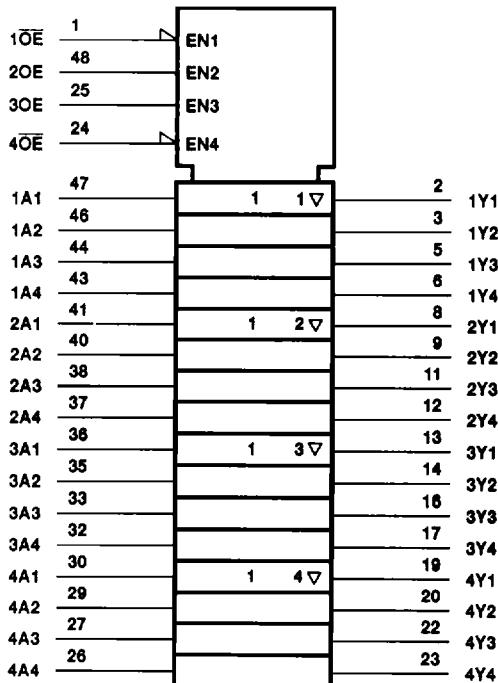
INPUTS		OUTPUTS
1 \bar{OE} , 4 \bar{OE}	1A, 4A	1Y, 4Y
L	H	H
L	L	L
H	X	Z

INPUTS		OUTPUTS
2 \bar{OE} , 3 \bar{OE}	2A, 3A	2Y, 3Y
H	H	H
H	L	L
L	X	Z

logic diagram (positive logic)



logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984
 and IEC Publication 617-12.

SN74LVC16241
16-BIT BUFFER/DRIVER
WITH 3-STATE OUTPUTS
SCAS348A - MARCH 1994 - REVISED JULY 1995

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC}	-0.5 V to 6.5 V
Input voltage range, V _I	-0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state or power-off state, V _O (see Note 1)	-0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V _O (see Notes 1 and 2)	-0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	-50 mA
Output clamp current, I _{OK} (V _O < 0 or V _O > V _{CC})	±50 mA
Continuous output current, I _O (V _O = 0 to V _{CC})	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Maximum power dissipation at T _A = 55°C (in still air) (see Note 3): DGG package	0.85 W
DL package	1.2 W
Storage temperature range, T _{STG}	-65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 2. This value is limited to 4.6 V maximum.
 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 ABT Advanced BiCMOS Technology Data Book, literature number SCBD002B.

recommended operating conditions (see Note 4)

		MIN	MAX	UNIT
V _{CC}	Supply voltage	Operating	2	3.8
		Data retention only	1.5	V
V _{IH}	High-level input voltage	V _{CC} = 2.7 V to 3.6 V	2	V
V _{IL}	Low-level input voltage	V _{CC} = 2.7 V to 3.6 V	0.8	V
V _I	Input voltage		0	5.5
V _O	Output voltage		0	V _{CC}
I _{OH}	High-level output current	V _{CC} = 2.7 V	-12	mA
		V _{CC} = 3 V	-24	
I _{OL}	Low-level output current	V _{CC} = 2.7 V	12	mA
		V _{CC} = 3 V	24	
Δt/ΔV	Input transition rise or fall rate		0	10 ns/V
T _A	Operating free-air temperature		-40	85 °C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.



SN74LVC16241
16-BIT BUFFER/DRIVER
WITH 3-STATE OUTPUTS
SCAS348A - MARCH 1994 - REVISED JULY 1995

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V _{CC} [†]	MIN	TYP‡	MAX	UNIT
V _{OH}	I _{OH} = -100 µA			MIN to MAX	V _{CC} -0.2		V
	I _{OH} = -12 mA			2.7 V	2.2		
	I _{OH} = -24 mA			3 V	2.4		
V _{OL}	I _{OL} = 100 µA			MIN to MAX		0.2	V
	I _{OL} = 12 mA			2.7 V		0.4	
	I _{OL} = 24 mA			3 V		0.55	
I _I	V _I = 5.5 V or GND			3.6 V		±5	µA
I _{I(hold)}	Data inputs	V _I = 0.8 V			75		µA
		V _I = 2 V			-75		
I _{OZ}	V _O = 5.5 V or GND			3.6 V		±10	µA
I _{CC}	V _I = V _{CC} or GND, I _O = 0			3.6 V		40	µA
ΔI _{CC}	One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND			2.7 V to 3.6 V		500	µA
C _i	V _I = V _{CC} or GND			3.3 V			pF
C _o	V _O = V _{CC} or GND			3.3 V			pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.